



Ordering in semiconductor alloys

J. E. Bernard, R. G. Dandrea, L. G. Ferreira, S. Froyen, S. H. Wei, and A. Zunger

Citation: [Applied Physics Letters](#) 56, 731 (1990); doi: 10.1063/1.102695

View online: <http://dx.doi.org/10.1063/1.102695>

View Table of Contents: <http://scitation.aip.org/content/aip/journal/apl/56/8?ver=pdfcov>

Published by the [AIP Publishing](#)

Articles you may be interested in

[Epitaxial growth of Si_{1-x-y}Ge_xC_y alloy layers on \(100\) Si by rapid thermal chemical vapor deposition using methylsilane](#)

[J. Vac. Sci. Technol. B](#) 14, 1660 (1996); 10.1116/1.589207

[Atomic antimony for molecular beam epitaxy of high quality III-V semiconductor alloys](#)

[J. Vac. Sci. Technol. B](#) 14, 2335 (1996); 10.1116/1.588854

[Dependence of the optical properties of semiconductor alloys on the degree of long range order](#)

[Appl. Phys. Lett](#) 62, 1937 (1993); 10.1063/1.109496

[Band gap narrowing in ordered and disordered semiconductor alloys](#)

[Appl. Phys. Lett](#) 56, 662 (1990); 10.1063/1.103307

[Ordering induced changes in the optical spectra of semiconductor alloys](#)

[Appl. Phys. Lett](#) 52, 311 (1988); 10.1063/1.99503

Ordering in semiconductor allows



